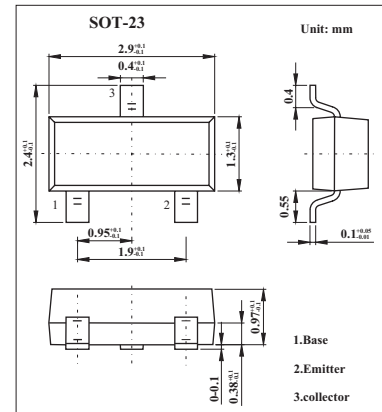


NPN Epitaxial Planar Silicon Transistor

2SC3134

■ Features

- High V_{EBO} .
- Wide ASO and high durability against breakdown.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	15	V
Collector current	I_C	150	mA
Collector current (pulse)	I_{CP}	300	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=10\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	90		560	
Gain bandwidth product	f_T	$V_{CE}=6\text{V}, I_C=1\text{mA}$		100		MHz
Output capacitance	C_{ob}	$V_{CB}=6\text{V}, f=1\text{MHz}$		2.2		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.5	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, R_{BE}=\infty$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	15			V

■ h_{FE} Classification

Marking	H			
Rank	4	5	6	7
h_{FE}	90~180	135~270	200~400	300~600